

NX3008PBK

30 V, 230 mA P-channel Trench MOSFET Rev. 1 — 1 August 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|------|------|
| V_{DS} | drain-source voltage | T _j = 25 °C | - | - | -30 | V |
| V_{GS} | gate-source voltage | | -8 | - | 8 | V |
| I_D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$ | [1] | - | -230 | mA |
| Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I_D = -200 mA; T_j = 25 °C | - | 2.8 | 4.1 | Ω |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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2. Pinning information

Table 2. Pinning information

| | • | | | |
|-----|--------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | G | gate | | |
| 2 | S | source | | D |
| 3 | D | drain | 1 | S 017aaa259 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | |
|-------------|----------|--|---------|--|
| | Name | Description | Version | |
| NX3008PBK | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| NX3008PBK | KT% |

^{[1] % =} placeholder for manufacturing site code.

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------------|---|-----|-----|------|------|
| V_{DS} | drain-source voltage | $T_j = 25 ^{\circ}C$ | | - | -30 | V |
| V _{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V_{GS} = -4.5 V; T_{amb} = 25 °C | [1] | - | -230 | mΑ |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -145 | mΑ |
| I _{DM} | peak drain current | $T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$ | | - | -1 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 350 | mW |
| | | | [1] | - | 420 | mW |
| | | T _{sp} = 25 °C | | - | 1140 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | diode | | | | | |
| Is | source current | T _{amb} = 25 °C | [1] | - | -230 | mA |
| ESD maximum | n rating | | | | | |
| V _{ESD} | electrostatic discharge voltage | НВМ | [3] | - | 2000 | V |

 $[\]label{eq:condition} \textbf{[1]} \quad \text{Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm2.}$

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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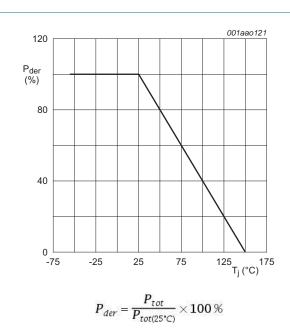


Fig 1. Normalized total power dissipation as a function of junction temperature

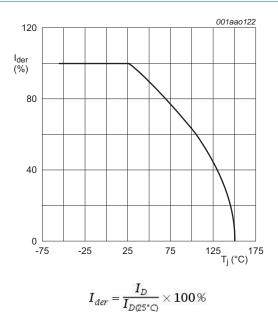
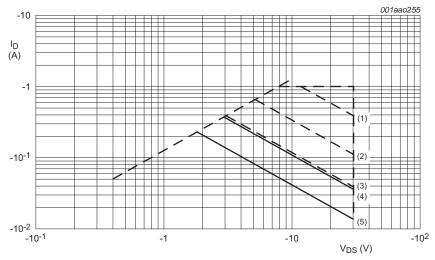


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} is a single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) $t_p = 10 \text{ ms}$
- (3) $t_p = 100 \text{ ms}$
- (4) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (5) DC; $T_{amb} = 25 \text{ °C}$; 1 cm² drain mounting pad

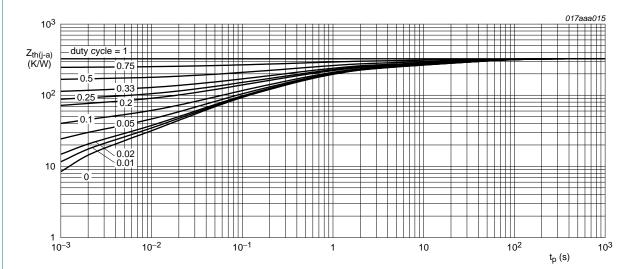
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

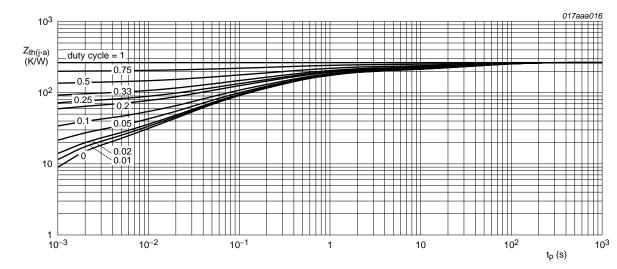
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | <u>[1]</u> _ | 310 | 370 | K/W |
| | | | [2] _ | 260 | 300 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | - | - | 115 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

| Table 7. | Characteristics | | | | | |
|---------------------|-----------------------------------|--|-------|-------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | -0.6 | -0.9 | -1.1 | V |
| I _{DSS} | drain leakage current | $V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | -10 | μΑ |
| | | $V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -0.2 | -1 | μΑ |
| | | $V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -0.2 | -1 | μΑ |
| | | $V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -10 | - | nΑ |
| | | $V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -10 | - | nΑ |
| | | $V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -1 | - | nΑ |
| | | $V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | -1 | - | nΑ |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$ | - | 2.8 | 4.1 | Ω |
| | | $V_{GS} = -4.5 \text{ V}; I_D = -200 \text{ mA}; T_j = 150 \text{ °C}$ | - | 5.3 | 7.8 | Ω |
| | | $V_{GS} = -2.5 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 \text{ °C}$ | - | 5.3 | 6.5 | Ω |
| 9 _{fs} | forward transconductance | $V_{DS} = -10 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$ | - | 160 | - | mS |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $V_{DS} = -15 \text{ V}; I_D = -200 \text{ mA};$ | - | 0.55 | 0.72 | nC |
| Q_{GS} | gate-source charge | $V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.23 | - | nC |
| Q_{GD} | gate-drain charge | | - | 0.09 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = -15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$ | - | 31 | 46 | pF |
| Coss | output capacitance | $T_j = 25 ^{\circ}\text{C}$ | - | 6.5 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 2.3 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -20 V; R_L = 250 Ω ; V_{GS} = -4.5 V; | - | 19 | 38 | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 30 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 65 | 130 | ns |
| t _f | fall time | | - | 38 | - | ns |
| Source-d | rain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = -200 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | -0.47 | -0.88 | -1.2 | V |

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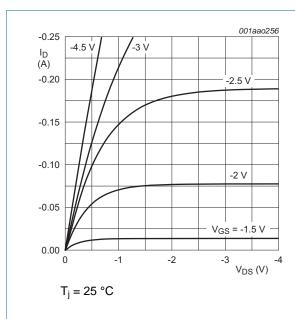
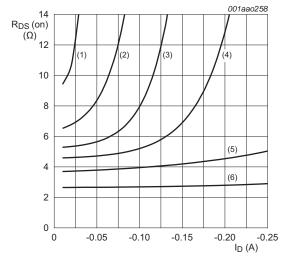


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_j = 25 °C

(1) $V_{GS} = -1.75 \text{ V}$

(2) $V_{GS} = -2.0 \text{ V}$

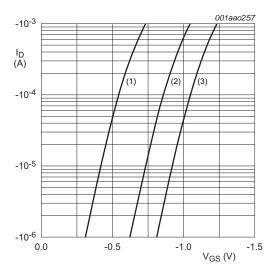
(3) $V_{GS} = -2.25 \text{ V}$

(4) $V_{GS} = -2.5 \text{ V}$

(5) $V_{GS} = -3.0 \text{ V}$

(6) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



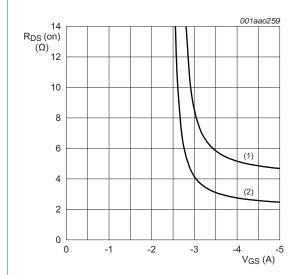
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



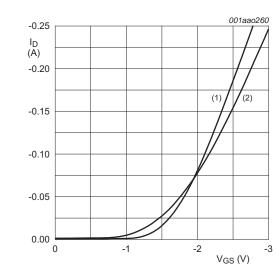
 $I_D = -200 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}\text{C}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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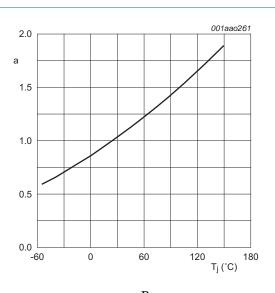


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

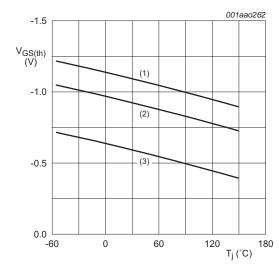
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

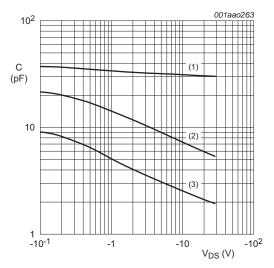
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

(1)C_{iss}

(2)C_{oss}

(3)C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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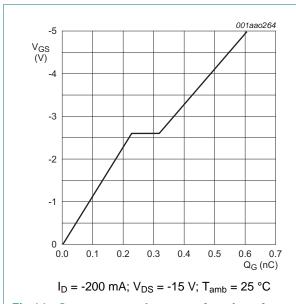


Fig 14. Gate-source voltage as a function of gate charge; typical values

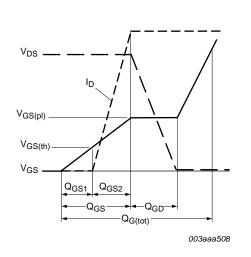
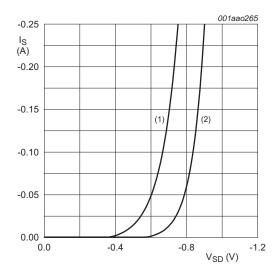


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

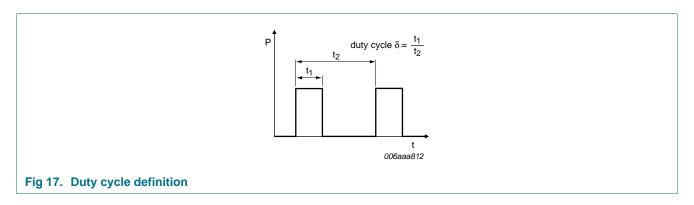
(1) $T_i = 150 \, ^{\circ}\text{C}$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

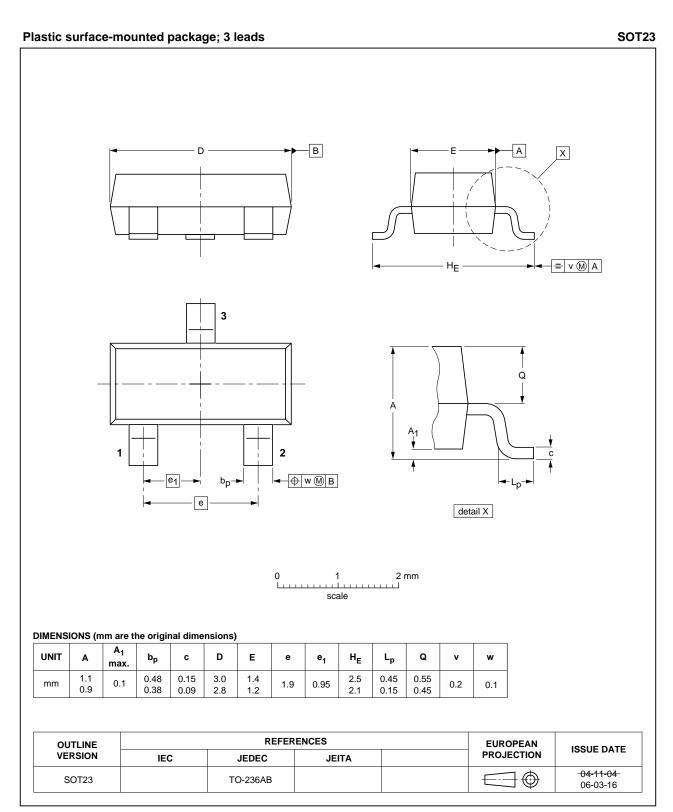
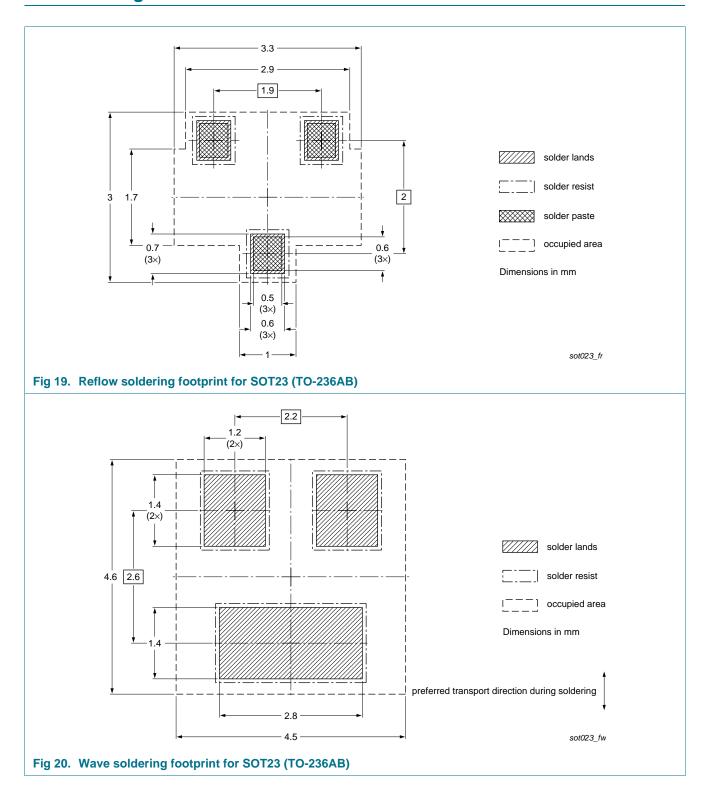


Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



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11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| NX3008PBK v.1 | 20110801 | Product data sheet | - | - |

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12. Legal information

12.1 Data sheet status

| Document status [1] [2] | Product status [3] | Definition |
|--------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

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- [2] The term 'short data sheet' is explained in section "Definitions"
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